

24N50

主要参数 MAIN CHARACTERISTICS

I_D	24 A
V_{DS}	500 V
$R_{ds(on)} (V_{GS}=10V)$	$<0.27\Omega$

用途

- 负载开关
- 脉宽调制
- 电源管理

APPLICATIONS

- Load Switch
- PWM Application
- Power Management

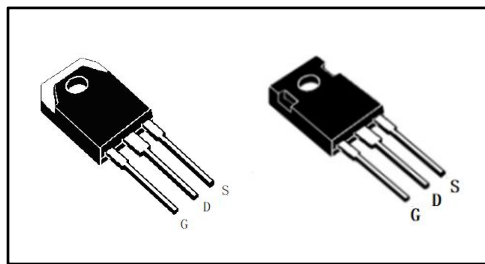
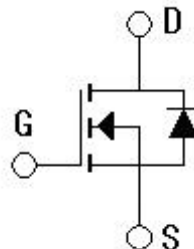
产品特性

- 符合环保标准
- 产品无卤素
- 湿敏等级3级

FEATURES

- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

封装 Package



产品中有毒有害物质或元素的名称及含量

部件名称	有害物质或元素					
	铅 (Pb)	汞 (Hg)	镉 (Cd)	六价铬 (Cr(VI))	多溴联苯 (PBB)	多溴二苯醚 (PBDE)
(含量要求)	$\leq 0.1\%$	$\leq 0.1\%$	$\leq 0.01\%$	$\leq 0.1\%$	$\leq 0.1\%$	$\leq 0.1\%$
引线框	○	○	○	○	○	○
塑封树脂	○	○	○	○	○	○
管芯	○	○	○	○	○	○
内引线	○	○	○	○	○	○
焊料	×	○	○	○	○	○
说明	○: 表示该元素的含量在 SJ/T11363-2006 标准的限量要求以下。 ×: 表示该元素的含量超出 SJ/T11363-2006 标准的限量要求。 目前产品的焊料中含有铅 (Pb) 成分, 但属于欧盟 RoHS 指令豁免范围。					

绝对最大额定值 **ABSOLUTE RATINGS** ($T_C=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高漏极-源极直流电压 Drain-Source Voltage	V_{DS}	500	V
连续漏极电流 Drain Current-continuous	I_D $T=25^{\circ}\text{C}$	24	A
最大脉冲漏极电流 Drain Current – pulse ^{Note 1}	I_{DM}	96	A
最高栅源电压 Gate-Source Voltage	V_{GS}	± 20	V
单脉冲雪崩能量 Single Pulsed Avalanche Energy ^{Note 2}	E_{AS}	1100	mJ
耗散功率 Power Dissipation	P_D $T_C=25^{\circ}\text{C}$	360	W
最高结温及存储温度 Operating and Storage Temperature Range	T_J, T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V, T_J=25^\circ C$	500	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V, T_C=25^\circ C$	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$	-	0.24	0.27	Ω
跨导 Forward Transconductance	gfs	$V_{DS}=25V, I_D=12A$	-	30	-	S
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	3060	-	pF
输出电容 Output capacitance	C_{oss}		-	290	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	17	-	pF

电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=250V, I_D=10A, R_G=25\Omega$ $V_{GS}=10V$	-	53	-	ns	
上升时间 Turn-On rise time	t_r		-	91	-	ns	
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	108	-	ns	
下降时间 Turn-Off Fall time	t_f		-	80	-	ns	
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=250V$, $I_D=12A$ $V_{GS} =10V$	-	46	-	nC	
栅-源电荷 Gate-Source charge	Q_{gs}		-	9	-	nC	
栅-漏电荷 Gate-Drain charge	Q_{gd}		-	20	-	nC	
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	24	A	
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V,$ $I_S=12A$	-	-	1.2	V	
反向恢复时间 Reverse Recovery Time	T_{RR}	$V_{GS} = 0V,$ $I_S = 12A, di_F/dt =100A/\mu s$	-	570	-	ns	
反向恢复电荷 Reverse Recovery Charge	Q_{RR}		-	6.1	-	μC	

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符号 Symbol	值 Value	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.51	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction-to-Ambient	$R_{th(j-A)}$	62.5	$^{\circ}C/W$

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 5mH, VDD = 30V, RG = 25 Ω , Starting TJ = 25 $^{\circ}C$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

特征曲线 ELECTRICAL CHARACTERISTICS

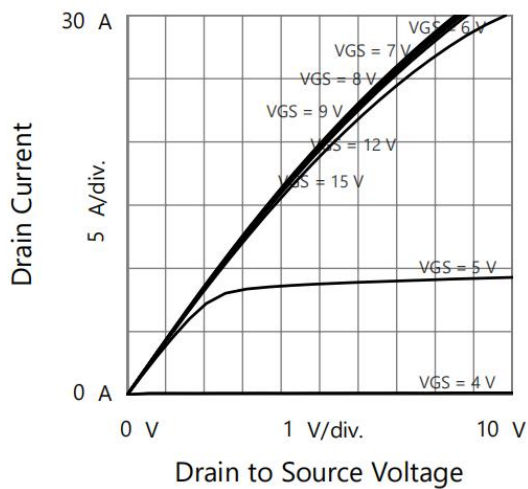
Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Transfer Characteristics

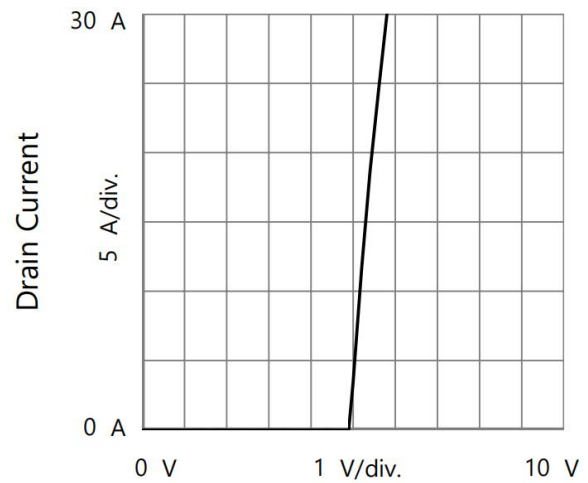


Figure 3. Drain to Source Resistance vs. Drain Current

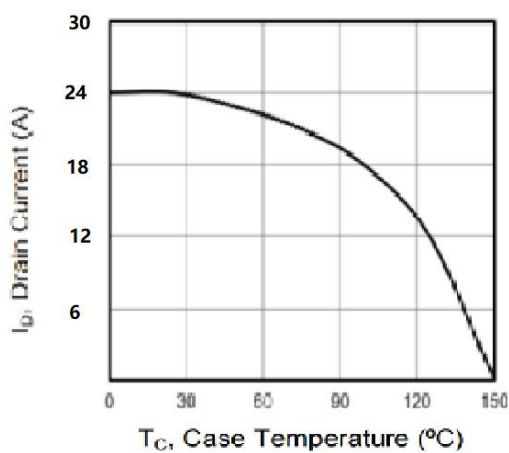
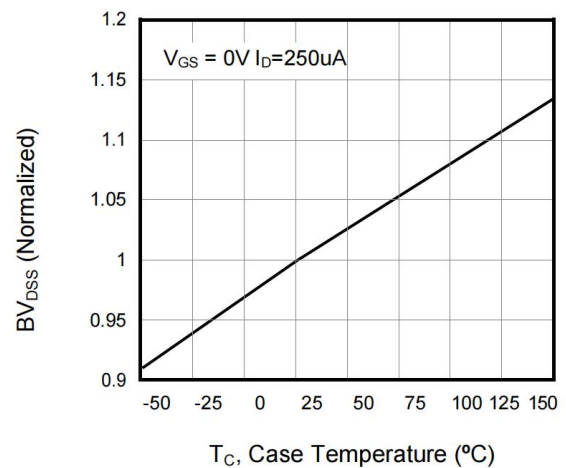
Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Drain to Source Voltage vs. Gate to Source Voltage

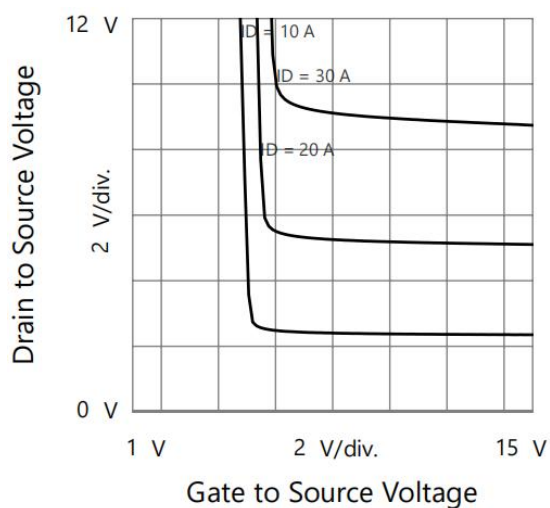
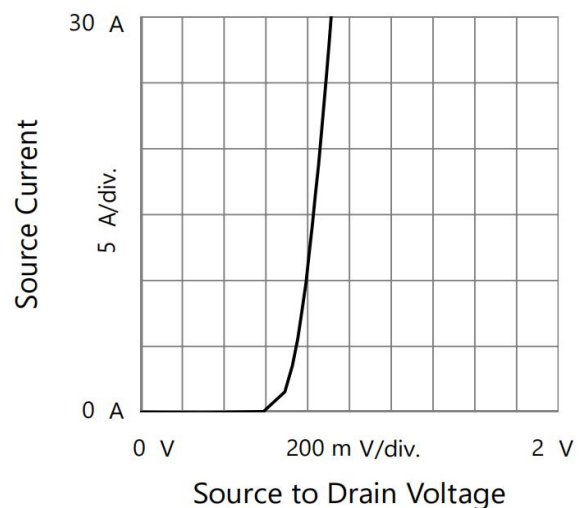


Figure 6. Body Diode Forward Characteristics



特征曲线 **ELECTRICAL CHARACTERISTICS**

Figure 7. Capacitance

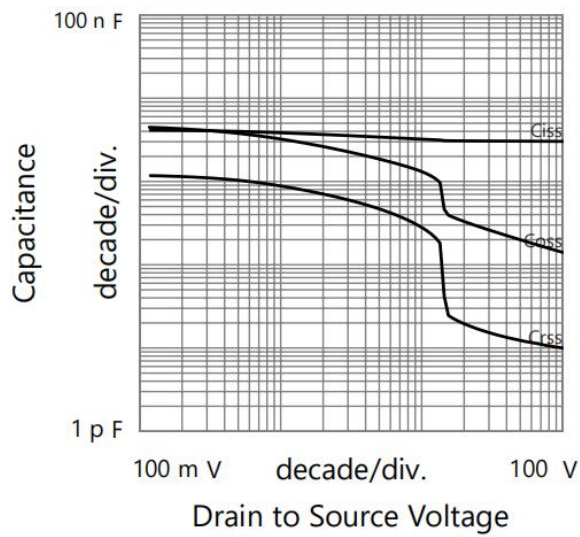


Figure 8. Gate Charge

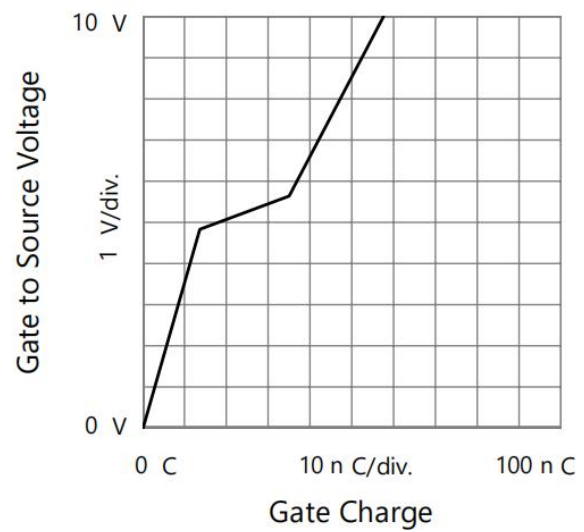
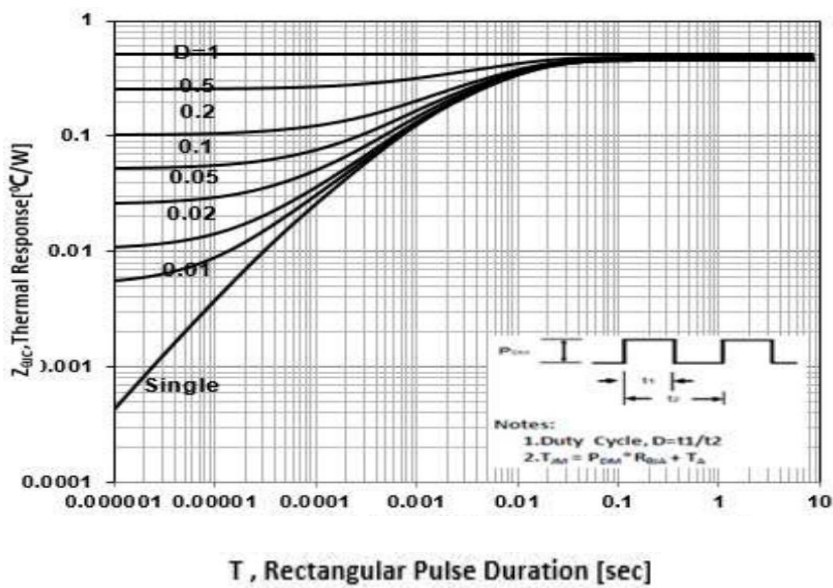
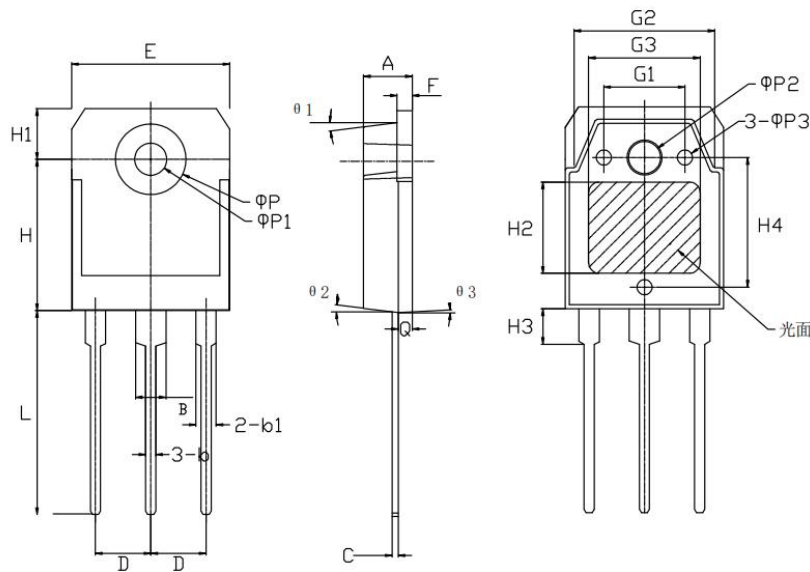


Figure 9. Transient Thermal Impedance



外形尺寸 PACKAGE MECHANICAL DATA

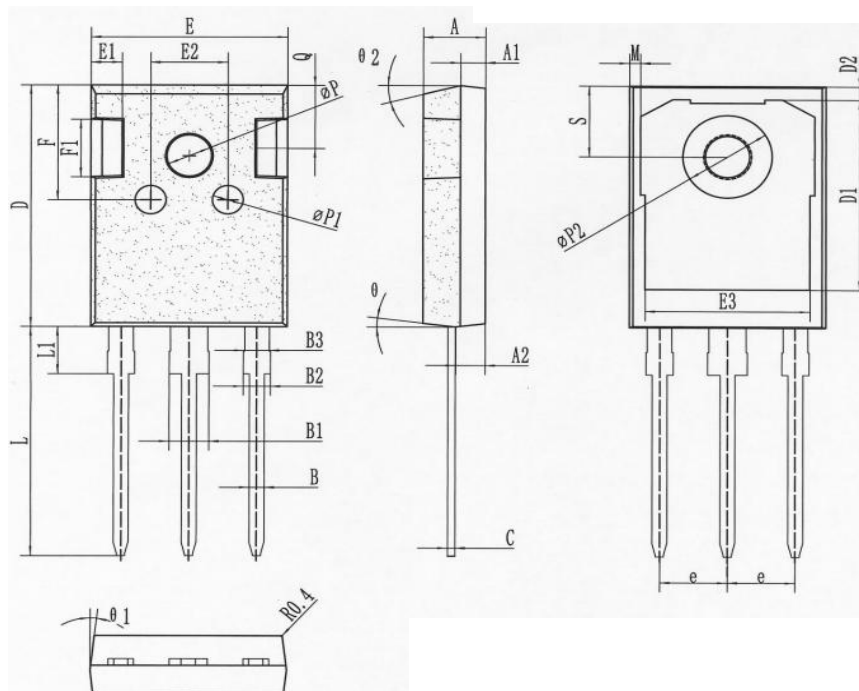
TO-3P



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.75	4.80	4.85
B	3.00	3.10	3.20
C	0.55	0.60	0.65
D	5.35	5.45	5.55
E	15.55	15.75	15.95
F	1.40	1.50	1.60
G1	7.90	8.00	8.10
G2	13.20	13.40	13.60
G3	10.90	11.00	11.10
b	0.85	1.00	1.15
b1	1.95	2.05	2.15
L	20.00	20.15	20.30
H	14.80	14.90	15.00
H1	4.90	5.00	5.10
H2	8.90	9.00	9.10
H3	3.20	3.50	3.80
H4	12.66	12.76	12.86
φP	6.90	7.00	7.10
φP1	3.10	3.20	3.30
φP2	3.40	3.50	3.60
φP3	1.40	1.50	1.60
θ1	6°	7°	8°
θ2	6°	7°	8°
θ3	2°	3°	4°
Q	1.33	1.38	1.43

TO-247



SYMBOL	MM		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	1.90	2.00	2.10
A2	2.30	2.40	2.50
B	1.15	1.20	1.25
B1	3.05	3.15	3.25
B2	2.00	2.10	2.20
B3	1.90	2.00	2.10
C	0.55	0.60	0.65
D	20.90	21.00	21.10
D1	16.35	16.55	16.75
D2	1.02	1.17	1.32
E	15.70	15.80	15.90
E1	2.40	2.50	2.60
E2	6.10	6.20	6.30
E3	13.10	13.30	13.50
F	9.80	10.00	10.20
F1	4.90	5.00	5.10
e	5.44 BSC		
L	19.72	19.92	20.12
L1	3.90	4.10	4.30
φP	3.50	3.60	3.70
φP1	2.40	2.50	2.60
φP2	7.10	7.20	7.30
S	6.05	6.15	6.25
M	0.45	—	0.95
Q	5.60	5.80	6.00
θ	5°	7°	9°
θ1	5°	7°	9°
θ2	13°	15°	17°